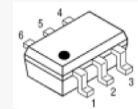


Features

- 19.5 dB Gain at 2 GHz
- 18 dBm P1dB at 2 GHz
- 30.5 dBm Output IP3 at 2 GHz
- 3.5 dB NF at 2 GHz
- MTTF > 100 Years
- Single Supply

Description

The ASW235, a power amplifier MMIC, has a high linearity, high gain, and high efficiency over a wide range of frequency, being suitable for use in both receiver and transmitter of telecommunication systems up to 6 GHz. The amplifier is available in a SOT363 package and passes through the stringent DC, RF, and reliability tests.



Package Style: SOT363

Typical Performance

(Supply Voltage = +4.65 V, T_A = +25 °C, Z₀ = 50 Ω)

Parameters	Units	Typical		
		900	2000	2700
Frequency	MHz			
Gain	dB	23.0	19.5	17.5
S11	dB	-13	-15	-18
S22	dB	-10	-12	-12
Output IP3 ¹⁾	dBm	29.0	30.5	30.0
Noise Figure	dB	3.3	3.5	3.9
Output P1dB	dBm	16	18	17
Current	mA	46	46	46
Device Voltage	V	+4.65	+4.65	+4.65

1) OIP3 is measured with two tones at an output power of +0 dBm/tone separated by 1 MHz.

Product Specifications

Parameters	Units	Min	Typ	Max
Testing Frequency	MHz		2000	
Gain	dB		19.5	
S11	dB		-15	
S22	dB		-12	
Output IP3	dBm		30.5	
Noise Figure	dB		3.5	
Output P1dB	dBm		18	
Current	mA		46	
Device Voltage	V		+4.65	

Absolute Maximum Ratings

Parameters	Rating
Operating Case Temperature	-40 to +85 °C
Storage Temperature	-40 to +150 °C
Device Voltage	+5.5 V
Operating Junction Temperature	+150 °C
Input RF Power (Continuous)	22 dBm

The operation of this device in excess of any of these limits may cause permanent damage.

* Refer to the max. input RF power data at <http://www.asb.co.kr/pdf/Maximum Input Power Analysis.pdf>. The max. input RF power, in principle, depends upon application frequency, matching circuit, and device voltage.

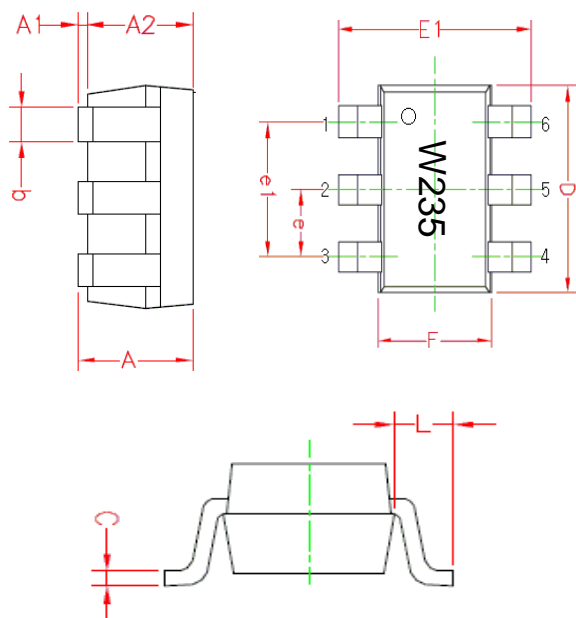
Application Circuit

- 5 ~ 140 MHz
- 500 ~ 2700 MHz
- IF

Pin Configuration

Pin No.	Function
1	RF OUT & Bias
2,3,5,6	GND
4	RF IN

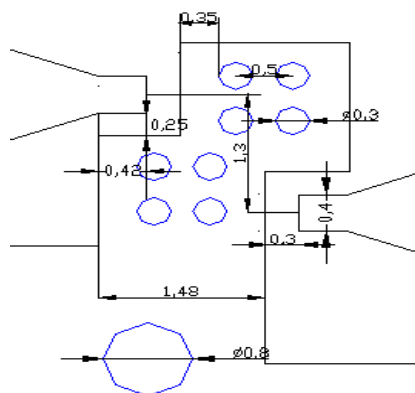
Outline Drawing



Symbols	Dimensions (In mm)		
	MIN	NOM	MAX
A	0.900	1.000	1.10
A1	0.025	0.062	0.10
A2	0.875	0.937	1.00
b	0.200	0.300	0.40
C	0.100	0.125	0.15
D	1.900	2.000	2.10
F	1.150	1.250	1.35
E1	2.000	2.100	2.20
e	--	0.65BSC	--
e1	--	1.30BSC	--
L	--	0.425REF	--

Pin NO.	Function	Pin NO.	Function.
1	RF OUT & Bias	4	RF IN
2	GND	5	GND
3	GND	6	GND

Mounting Recommendation



- Note:**
1. The number and size of ground via holes in a circuit board is critical for thermal and RF grounding considerations.
 2. We recommend that the ground via holes be placed on the bottom of lead pin 2 for better RF and thermal performance, as shown in the drawing at the left side.

ESD Classification & Moisture Sensitivity Level

ESD Classification

HBM	Class 1A Voltage Level: 400 V
MM	Class A Voltage Level: 50 V

CAUTION: Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices

Moisture Sensitivity Level (MSL)

Level 3 at 260 °C reflow

APPLICATION CIRCUIT

IF

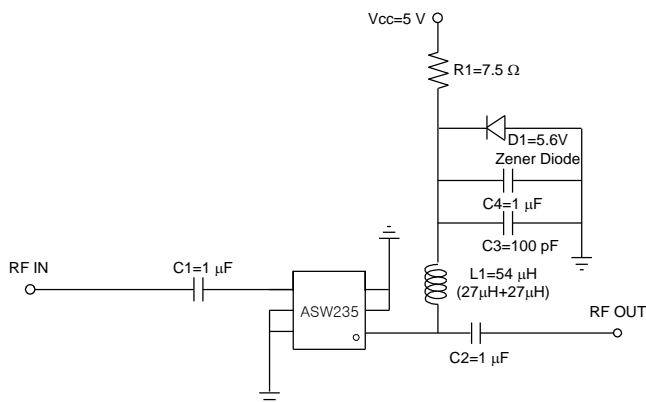
5 ~ 140 MHz

+5 V

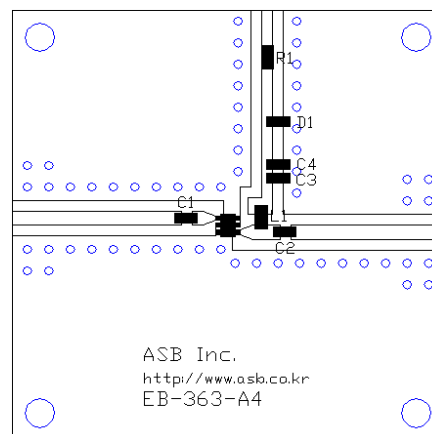
Frequency (MHz)	5	140
Magnitude S21 (dB)	24.5	24.5
Magnitude S11 (dB)	-17	-17
Magnitude S22 (dB)	-8	-8
Output P1dB (dBm)	14	14
Output IP3 ¹⁾ (dBm)	25.5	25.5
Noise Figure (dB)	3.3	3.3
Device Voltage (V)	+4.65	+4.65
Current (mA)	46	46

1) OIP3 is measured with two tones at an output power of +0 dBm/tone separated by 1 MHz.

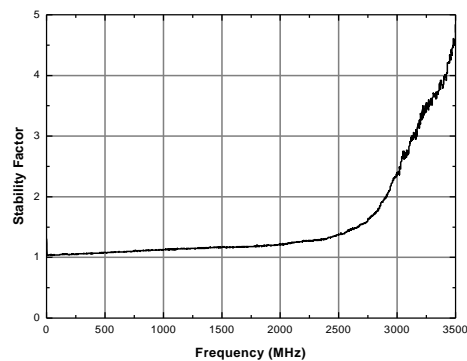
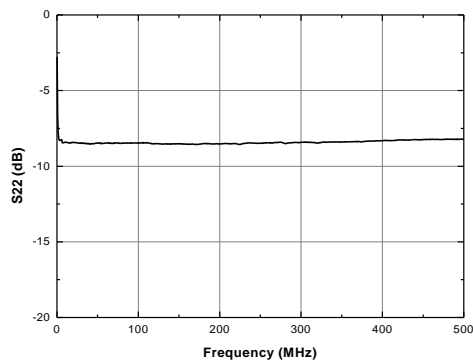
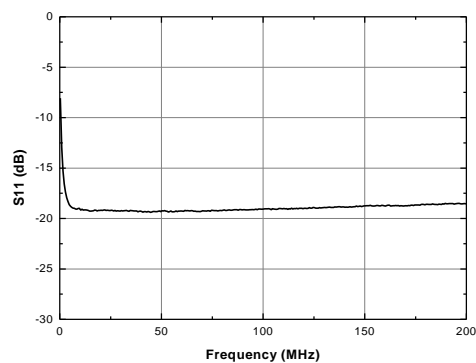
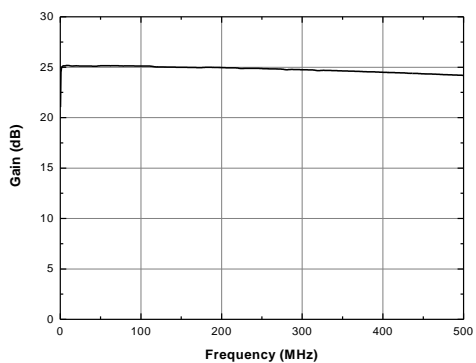
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

Wide Band

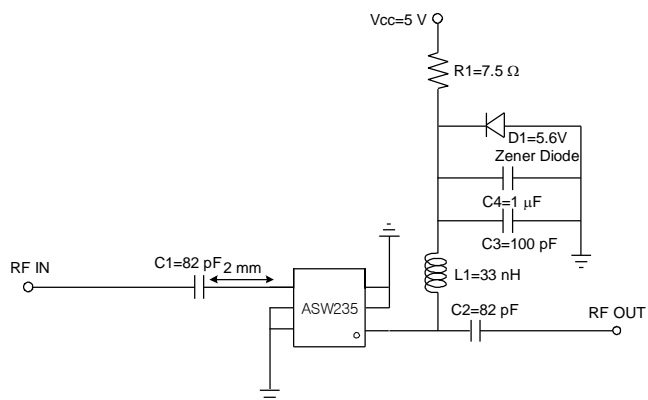
500 ~ 2700 MHz

+5 V

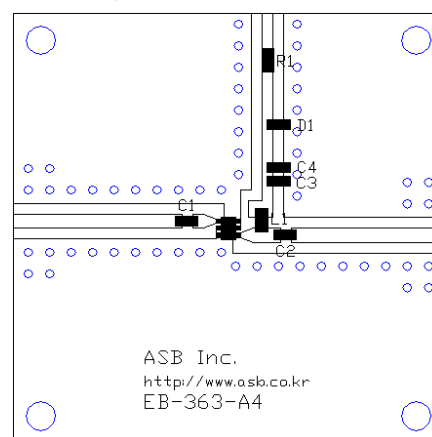
Frequency (MHz)	900	2000	2700
Magnitude S21 (dB)	23.0	19.5	17.5
Magnitude S11 (dB)	-13	-15	-18
Magnitude S22 (dB)	-10	-12	-12
Output P1dB (dBm)	16	18	17
Output IP3 ¹⁾ (dBm)	29.0	30.5	30.0
Noise Figure (dB)	3.3	3.5	3.9
Device Voltage (V)	+4.65	+4.65	+4.65
Current (mA)	46	46	46

1) OIP3 is measured with two tones at an output power of +0 dBm/tone separated by 1MHz.

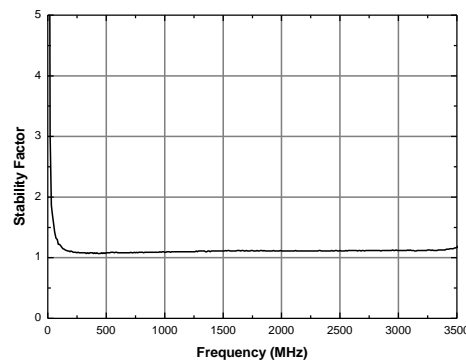
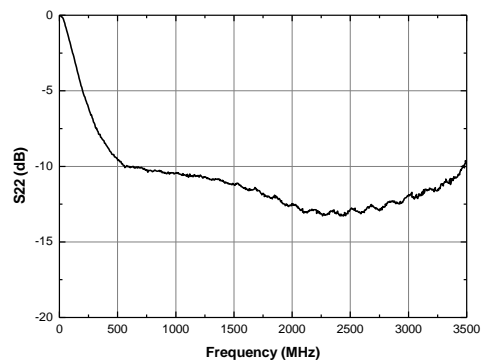
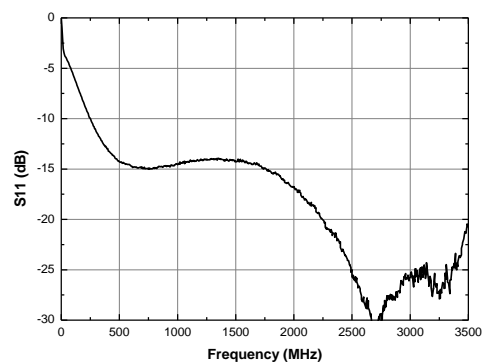
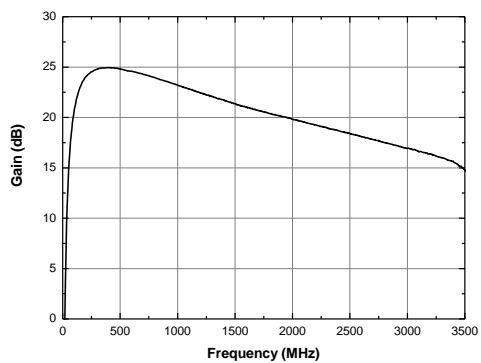
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

Wide Band

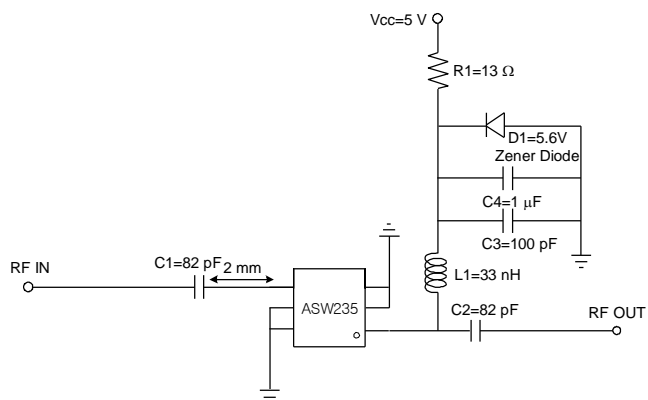
500 ~ 2700 MHz

+5 V, 36 mA

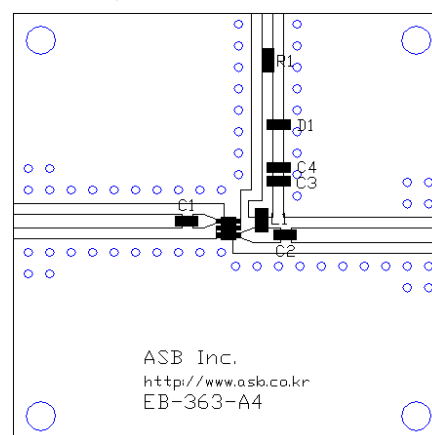
Frequency (MHz)	900	2000	2700
Magnitude S21 (dB)	22.5	19.0	17.0
Magnitude S11 (dB)	-13	-15	-18
Magnitude S22 (dB)	-9	-12	-11
Output P1dB (dBm)	13	16	16
Output IP3 ¹⁾ (dBm)	25.5	28.0	29.0
Noise Figure (dB)	3.2	3.4	3.8
Device Voltage (V)	+4.3	+4.3	+4.3
Current (mA)	36	36	36

1) OIP3 is measured with two tones at an output power of +0 dBm/tone separated by 1MHz.

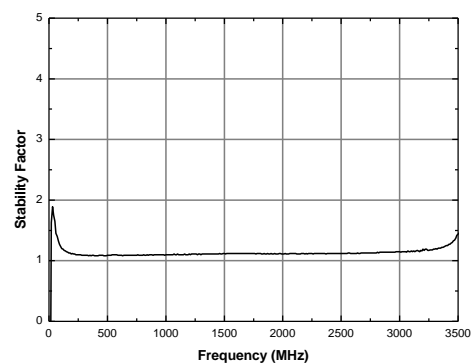
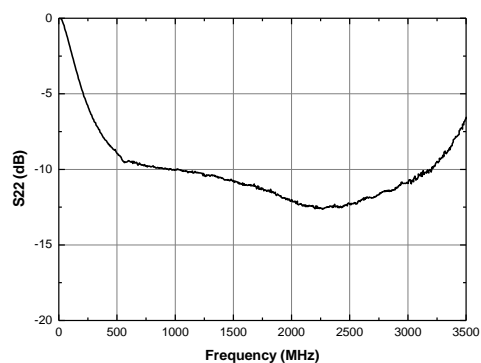
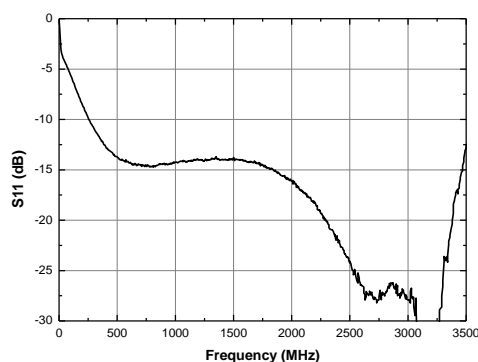
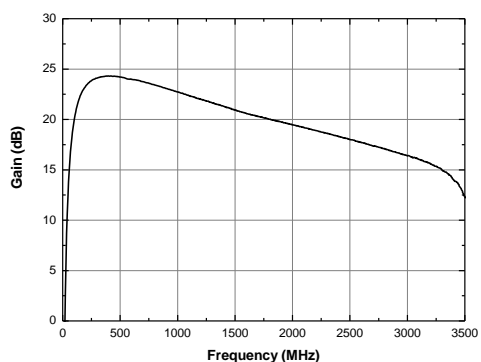
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



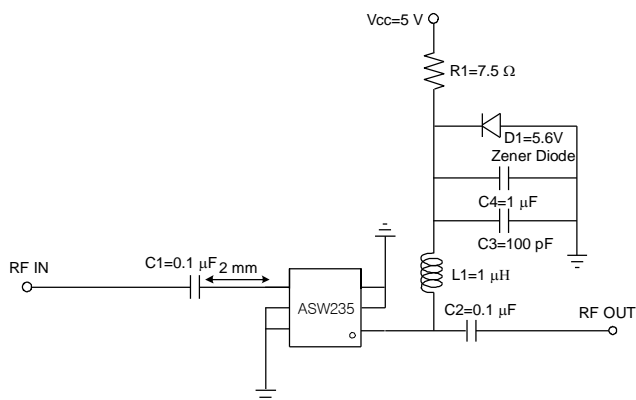
APPLICATION CIRCUIT

IF
50 ~ 450 MHz
+5 V

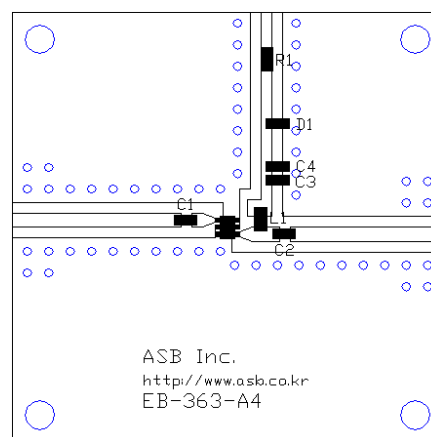
Frequency (MHz)	70	150	300
Magnitude S21 (dB)	24	24	24
Magnitude S11 (dB)	-12	-12	-12
Magnitude S22 (dB)	-8	-8	-8
Output P1dB (dBm)	15	15	16
Output IP3 ¹⁾ (dBm)	27	28	29
Noise Figure (dB)	3.3	3.3	3.4
Device Voltage (V)	+4.65	+4.65	+4.65
Current (mA)	46	46	46

1) OIP3 is measured with two tones at an output power of +0 dBm/tone separated by 1MHz.

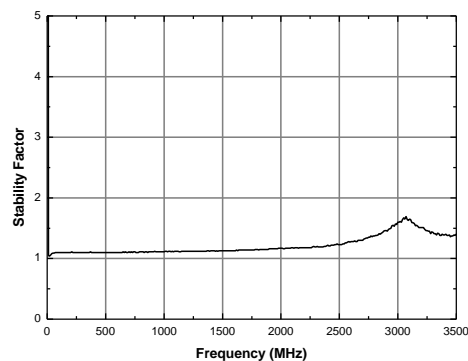
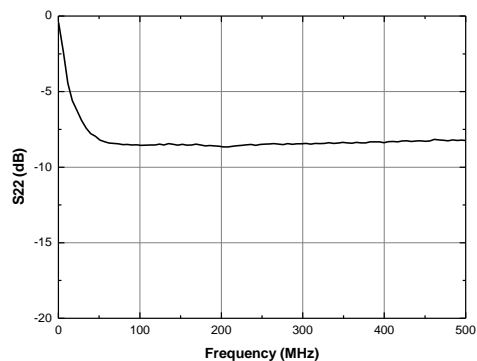
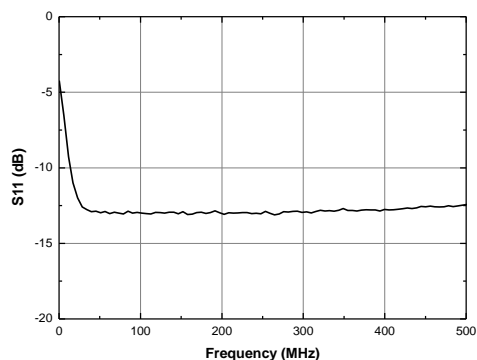
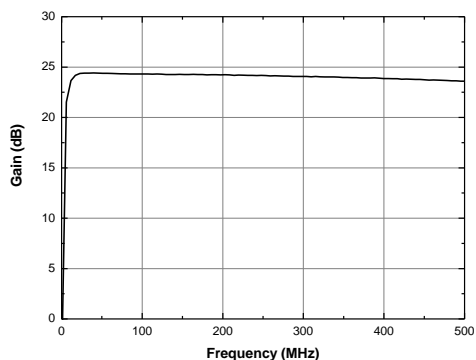
Schematic



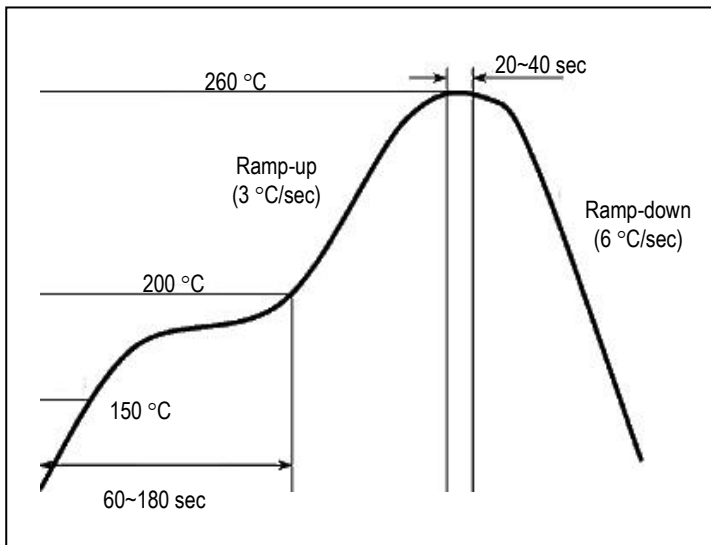
Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



Recommended Soldering Reflow Profile



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